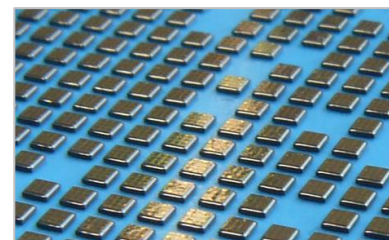




ELC-1300-27

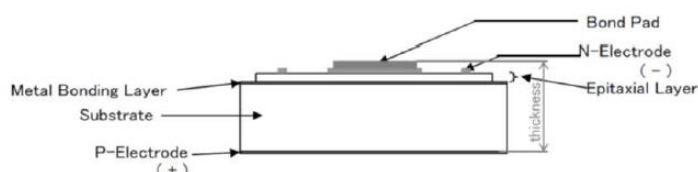
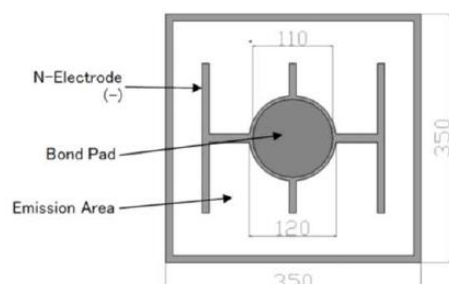
- Infrared LED bare chip die
- 1300 nm
- InGaAs
- n-side up
- RoHS compliant



Electro-Optical Characteristics (T_{CASE} = 25°C)

Parameter	Condition	Symbol	Values			Unit
			Min.	Typ.	Max.	
Peak Wavelength	I _F =20 mA	λ _p		1270		nm
Output Power (bare die on TO-18 header)	I _F =20 mA	P _O		4		mW
Output Power (epoxy covered die on TO-18 header)	I _F =20 mA	P _O		7.2		mW
FWHM	I _F =20 mA	Δλ _{0.5}		72		nm
Forward Voltage	I _F =20 mA	V _F		0.96		V
Peak Wavelength	I _F =50 mA	λ _p		1276		nm
Output Power (epoxy covered die on TO-18 header)	I _F =50 mA	P _O		13.9		mW
FWHM	I _F =50 mA	Δλ _{0.5}		82		nm
Forward Voltage	I _F =50 mA	V _F		1.0		V
Peak Wavelength	I _F =100 mA	λ _p		1290		nm
Output Power (epoxy covered die on TO-18 header)	I _F =100 mA	P _O		19.5		mW
FWHM	I _F =100 mA	Δλ _{0.5}		95		nm
Forward Voltage	I _F =100 mA	V _F		1.1		V

Outline Dimensions



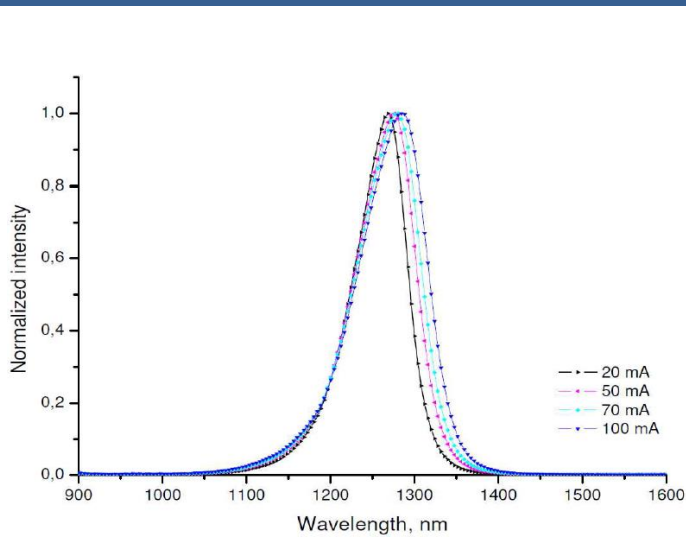
All dimensions in μm

Die size	typ. 0.350 x 0.350 mm (14 mil)
Die thickness	typ. 0.180 mm (7 mil)
Bond pad size	Ø 0.110 mm
Contact metallization	gold alloy

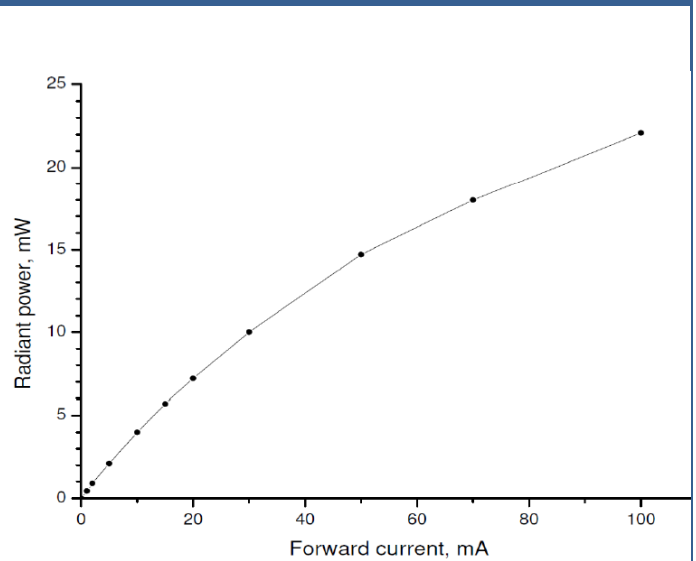


Outline Dimensions

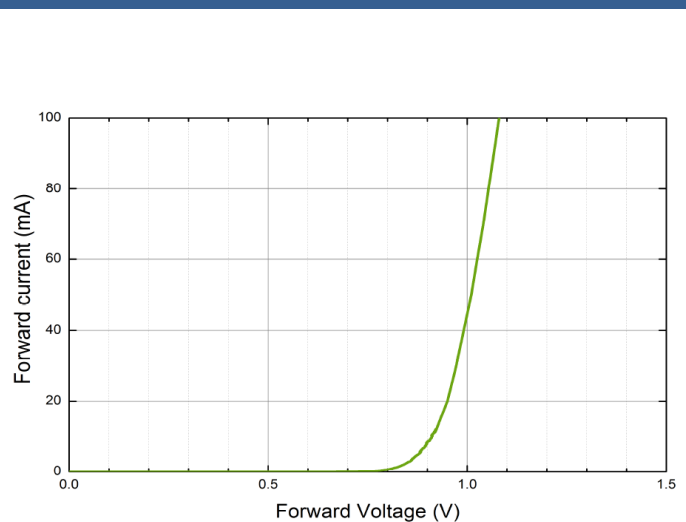
Spectral emission



Radiant power vs. Forward current



Forward current vs Forward voltage



/

/